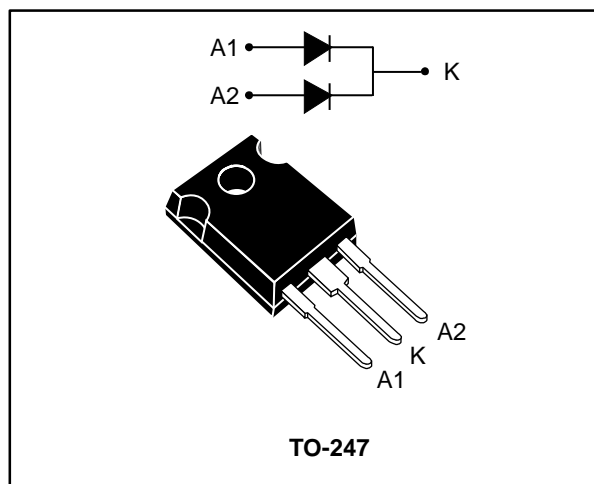


Automotive 650 V power Schottky silicon carbide diode

Datasheet - production data



Description

The SiC diode is a high voltage power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Used as a freewheeling or output rectification diode, this rectifier will enhance the performance and form factor of the targeted power supply or inverter.

Table 1: Device summary

| Symbol | Value |
|--------------|----------|
| $I_{F(AV)}$ | 2 x 20 A |
| V_{RRM} | 650 V |
| T_j (max.) | 175 °C |
| V_F (typ.) | 1.30 V |

Features

- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- Dedicated to PFC applications
- AEC-Q101 qualified
- PPAP capable
- ECOPACK®2 compliant component

1 Characteristics

Table 2: Absolute ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

| Symbol | Parameter | | Value | Unit |
|---------------------|--|--|-------------|------|
| V _{RRM} | Repetitive peak reverse voltage (T _j = -40 °C to +175 °C) | | 650 | V |
| I _{F(RMS)} | Forward rms current | | 40 | A |
| I _{F(AV)} | Average forward current | T _c = 140 °C ⁽¹⁾ , DC, per diode | 20 | A |
| | | T _c = 130 °C ⁽¹⁾ , DC, per device | 40 | |
| I _{FRM} | Repetitive peak forward current | T _c = 140 °C, T _j = 175 °C, δ = 0.1 | 87 | A |
| I _{FSM} | Surge non repetitive forward current | t _p = 10 ms sinusoidal, T _c = 25 °C | 90 | A |
| | | t _p = 10 ms sinusoidal, T _c = 125 °C | 70 | |
| | | t _p = 10 μs square, T _c = 25 °C | 400 | |
| T _{stg} | Storage temperature range | | -55 to +175 | °C |
| T _j | Operating junction temperature ⁽²⁾ | | -40 to +175 | °C |

Notes:

⁽¹⁾Value based on R_{th(j-c)} max.

⁽²⁾(dP_{tot}/dT_j) < (1/R_{th(j-a)}) condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Thermal parameters

| Symbol | Parameter | | Value | Unit |
|----------------------|------------------|-----------|-------|------|
| R _{th(j-c)} | Junction to case | Per diode | 0.90 | °C/W |
| | | Total | 0.60 | |
| R _{th(c)} | Coupling | | 0.30 | |

Table 4: Static electrical characteristics (per diode)

| Symbol | Parameter | Test conditions | | Min. | Typ. | Max. | Unit |
|-------------------------------|-------------------------|-------------------------|-----------------------------------|------|------|------|------|
| I _R ⁽¹⁾ | Reverse leakage current | T _j = 25 °C | V _R = V _{RRM} | - | 30 | 300 | μA |
| | | T _j = 150 °C | | - | 280 | 2000 | |
| | | T _j = 25 °C | V _R = 600 V | | 15 | 150 | |
| V _F ⁽²⁾ | Forward voltage drop | T _j = 25 °C | I _F = 20 A | - | 1.30 | 1.45 | V |
| | | T _j = 150 °C | | - | 1.45 | 1.65 | |
| | | T _j = 175 °C | | - | 1.50 | | |

Notes:

⁽¹⁾Pulse test: t_p = 5 ms, δ < 2%

⁽²⁾Pulse test: t_p = 500 μs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 1.02 \times I_{F(AV)} + 0.039 \times I_{F(RMS)}^2$$

Table 5: Dynamic electrical characteristics (per diode)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------|-------------------------|---|------|------|------|------|
| $Q_{Cj}^{(1)}$ | Total capacitive charge | $V_R = 400 \text{ V}$ | - | 62 | - | nC |
| C_j | Total capacitance | $V_R = 0 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$ | - | 1250 | - | pF |
| | | $V_R = 400 \text{ V}, T_c = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$ | - | 100 | - | |

Notes:

⁽¹⁾Most accurate value for the capacitive charge: $Q_{Cj} = \int_0^{V_{OUT}} C_j(V_R) \cdot dV_R$

1.1 Characteristics (curves)

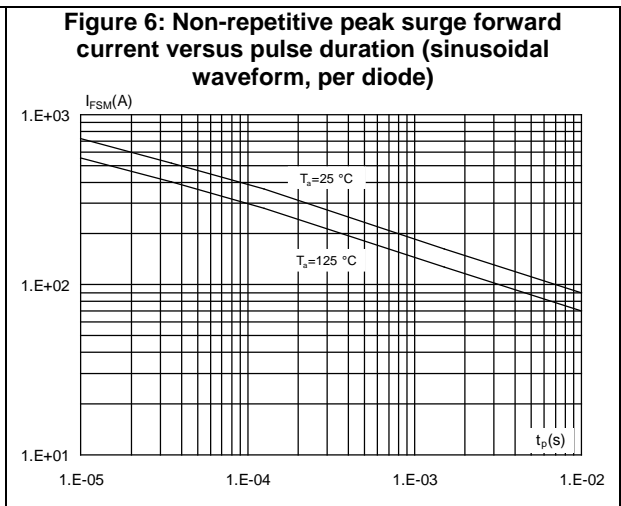
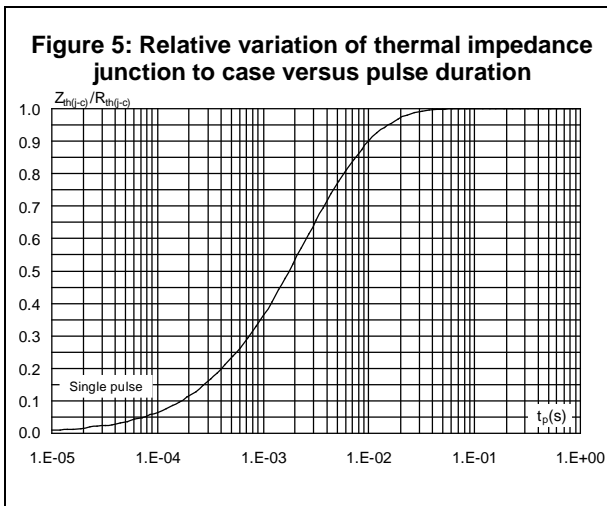
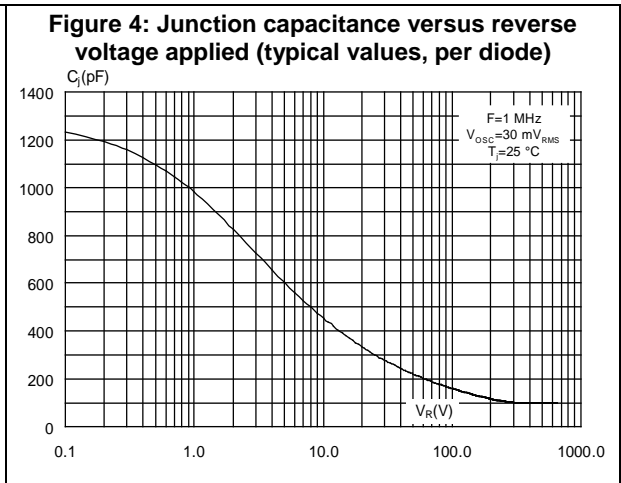
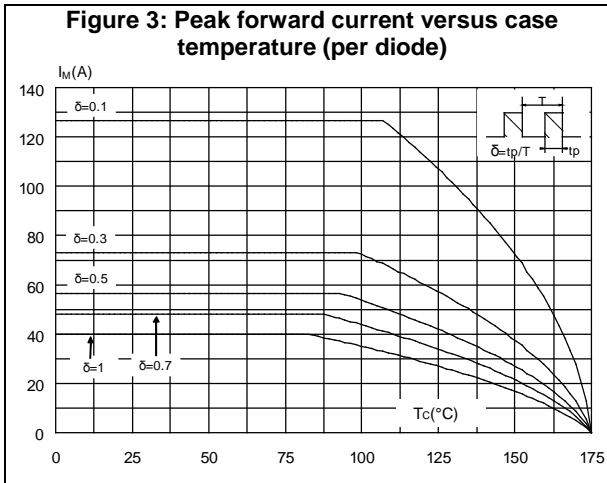
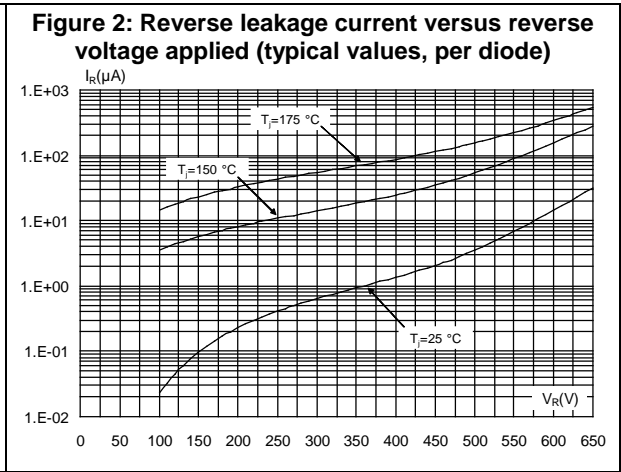
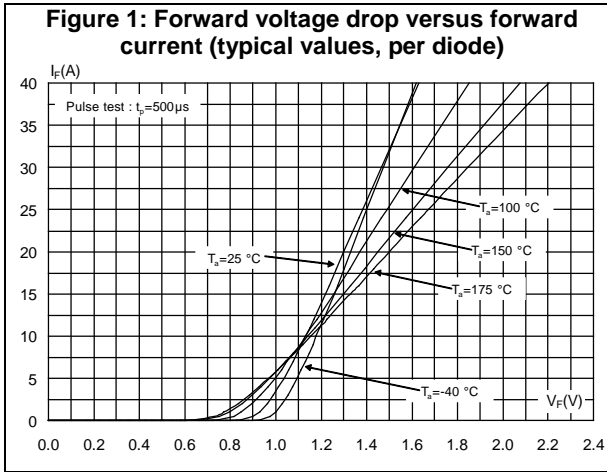


Figure 7: Total capacitive charges versus reverse voltage applied (typical values, per diode)

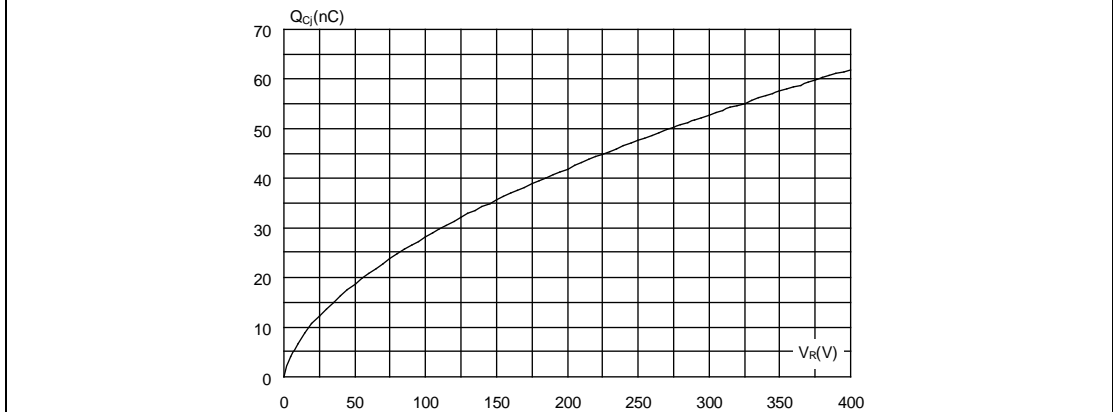


Table 6: TO-247 package mechanical data

| Ref. | Dimensions | | | | | |
|-------------------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 4.85 | | 5.15 | 0.191 | | 0.203 |
| A1 | 2.20 | | 2.60 | 0.086 | | 0.102 |
| b | 1.00 | | 1.40 | 0.039 | | 0.055 |
| b1 | 2.00 | | 2.40 | 0.078 | | 0.094 |
| b2 | 3.00 | | 3.40 | 0.118 | | 0.133 |
| c | 0.40 | | 0.80 | 0.015 | | 0.031 |
| D ⁽¹⁾ | 19.85 | | 20.15 | 0.781 | | 0.793 |
| E | 15.45 | | 15.75 | 0.608 | | 0.620 |
| e | 5.30 | 5.45 | 5.60 | 0.209 | 0.215 | 0.220 |
| L | 14.20 | | 14.80 | 0.559 | | 0.582 |
| L1 | 3.70 | | 4.30 | 0.145 | | 0.169 |
| L2 | | 18.50 | | | 0.728 | |
| ØP ⁽²⁾ | 3.55 | | 3.65 | 0.139 | | 0.143 |
| ØR | 4.50 | | 5.50 | 0.177 | | 0.217 |
| S | 5.30 | 5.50 | 5.70 | 0.209 | 0.216 | 0.224 |

Notes:

⁽¹⁾Dimension D plus gate protusion does not exceed 20.5 mm

⁽²⁾Resin thickness around the mounting hole is not less than 0.9 mm.

3 Ordering information

Table 7: Ordering information

| Order code | Marking | Package | Weight | Base qty. | Delivery mode |
|---------------|-------------|---------|--------|-----------|---------------|
| STPSC40065CWY | PSC40065CWY | TO-247 | 4.43 g | 30 | Tube |

4 Revision history

Table 8: Document revision history

| Date | Revision | Changes |
|-------------|----------|------------------------------|
| 11-May-2016 | 1 | First issue. |
| 12-May-2016 | 2 | Updated cover page footnote. |

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